



50V NPN LOW SATURATION TRANSISTOR

Features

- BV_{CEO} > 50V
- I_C = 4A Continuous Collector Current
- Low Saturation Voltage (100mV Max @1A)
- R_{SAT} = 68mΩ for a Low Equivalent On-Resistance
- h_{FE} Specified up to 6A for High Current Gain Hold Up
- Low Profile 0.6mm High Package for Thin Applications
- R_{θJA} Efficient, 60% Lower than SOT23
- 4mm² Footprint, 50% Smaller than SOT23
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXTN619MAQ)

Mechanical Data

- Case: U-DFN2020-3
- Nominal Package Height: 0.6mm
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.01 grams (Approximate)

Applications

- MOSFET Gate Driving
- DC-DC Converters
- Charging Circuits
- Motor Control
- Power Switches

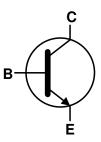
U-DFN2020-3 (Type B)



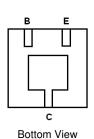




Bottom View



Device Symbol



Pin-Out

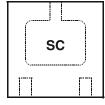
Ordering Information (Note 4)

I	Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
	ZXTN619MATA	SC	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Top View

SC = Product Type Marking code



Absolute Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Parameter		Symbol	Limit	Unit	
Collector-Base Voltage		V_{CBO}	100		
Collector-Emitter Voltage		V _{CEO}	50	V	
Emitter-Base Voltage		V_{EBO}	7		
Peak Pulse Current		Ісм	6		
Continuous Collector Current (Note 5) (Note 6)			4		
		IC	4.3	A	
Base Current		I _B	1		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	e Unit		
Power Dissipation	(Note 5)		1.5 12	W	
Linear Derating Factor	(Note 6)	P _D	2.45 19.6	mW/°C	
Thermal Pagistanes, Junation to Ambient	(Note 5)	В	83		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	51	°C/W	
Thermal Resistance, Junction to Lead	(Note 7)	$R_{ heta JL}$	16.8		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

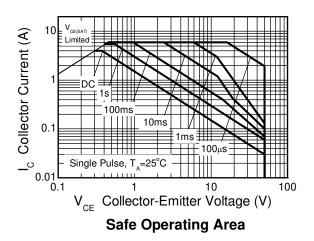
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

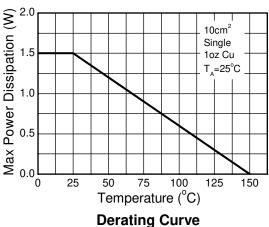
Notes:

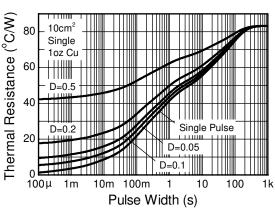
- 5. For a device mounted with the exposed collector pad on 31mm x 31mm (10cm²) 1oz copper that is on a single sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state. The entire exposed collector pad is attached to the heatsink.
 6. Same as Note 5, except the device is measured at t ≤ 5s.
 7. Thermal resistance from junction to solder-point (on the exposed collector pad).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

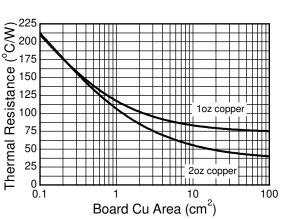


Thermal Characteristics and Derating Information



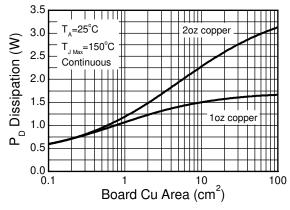






Transient Thermal Impedance

Thermal Resistance v Board Area



Power Dissipation v Board Area



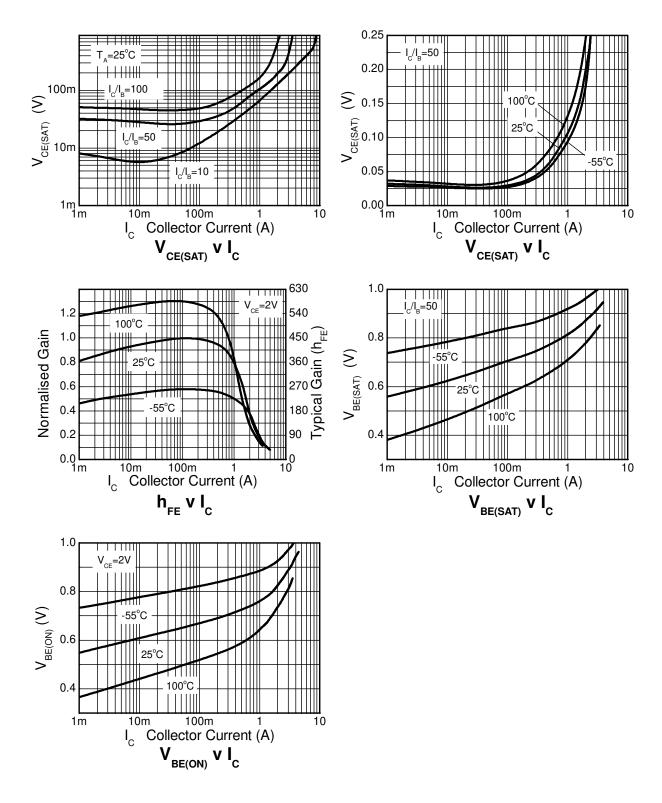
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	100	190	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	50	65	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.2	_	V	$I_E = 100\mu A$
Collector Cutoff Current	I _{CBO}	_	_	100	nA	V _{CB} = 80V
Emitter Cutoff Current	I _{EBO}	_	_	20	nA	V _{EB} = 6V
Collector Emitter Cutoff Current	I _{CES}	_	_	100	nA	V _{CES} = 40V
Static Forward Current Transfer Ratio (Note 9)	h _{FE}	200 300 200 100	400 450 400 225 40	_ _ _ _	_	$I_C = 10 \text{mA}, V_{CE} = 2 \text{V}$ $I_C = 200 \text{mA}, V_{CE} = 2 \text{V}$ $I_C = 1 \text{A}, V_{CE} = 2 \text{V}$ $I_C = 2 \text{A}, V_{CE} = 2 \text{V}$ $I_C = 6 \text{A}, V_{CE} = 2 \text{V}$
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(SAT)}		10 70 145 150 225 270	20 100 200 220 300 320	mV	$\begin{split} &I_{C}=0.1\text{A},\ I_{B}=10\text{mA}\\ &I_{C}=1\text{A},\ I_{B}=50\text{mA}\\ &I_{C}=1\text{A},\ I_{B}=10\text{mA}\\ &I_{C}=2\text{A},\ I_{B}=50\text{mA}\\ &I_{C}=3\text{A},\ I_{B}=100\text{mA}\\ &I_{C}=4\text{A},\ I_{B}=200\text{mA} \end{split}$
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(ON)}$	_	0.94	1.00	V	$I_C = 4A$, $V_{CE} = 2V$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(SAT)}$	_	1.00	1.07	V	$I_C = 4A$, $I_B = 200mA$
Output Capacitance	C _{OBO}	_	12	20	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	f⊤	100	165	_	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Turn-On Time	t _{ON}	_	170		ns	V _{CC} = 10V, I _C = 1A
Turn-Off Time	t _{OFF}	_	750	_	ns	$I_{B1} = -I_{B2} = 10 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

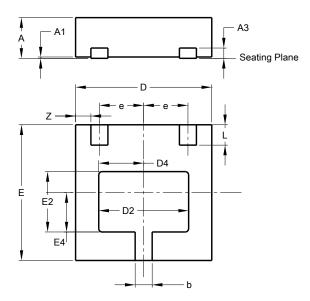




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-3 (Type B)

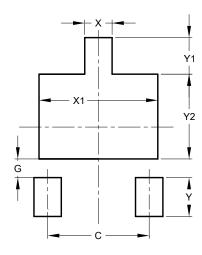


U-DFN2020-3						
(Type B)						
Dim	Min	Max	Тур			
Α	0.57	0.63	0.60			
A 1	0.00	0.05	0.02			
A3			0.152			
b	0.20	0.30	0.25			
D	1.950	2.075	2.00			
D2	1.22	1.42	1.32			
D4	0.56	0.76	0.66			
Е	1.950	2.075	2.00			
E2	0.79	0.99	0.89			
E4	0.48	0.68	0.58			
е	_		0.65			
L	0.25	0.35	0.30			
Z	_		0.225			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-3 (Type B)



Dimensions	Value		
Dimensions	(in mm)		
С	1.300		
G	0.240		
X	0.350		
X1	1.520		
Υ	0.500		
Y1	0.470		
Y2	1.090		



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